MJ N-Channel Super Trench Power MOSFET

Description

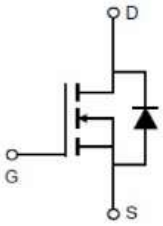
The MJXP01T10G uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Qg. This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS}=100V,I_D=105A
  $R_{DS(ON)}$=5.6mΩ (typical) @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150°C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram

Top View

Bottom View

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJXP01T10G	MJXP01T10G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	105	A
Drain Current-Continuous(T_C =100℃)	$I_{D(100℃)}$	74	A
Pulsed Drain Current	I_{DM}	400	A
Maximum Power Dissipation	P_D	135	W
Derating factor		1.1	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	676	mJ
Operating Junction and Storage Temperature Range	T_J ,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	0.93	℃/W

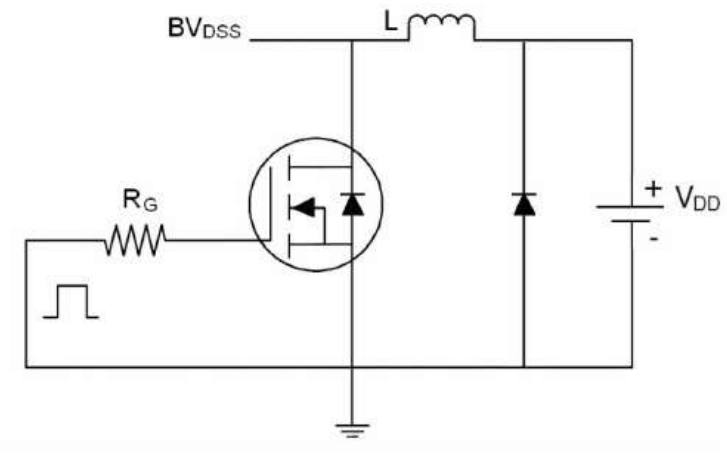
Electrical Characteristics (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} ,I_D=250μA	2.5	-	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=50A	-	5.6	6.4	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=50A	40	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V F=1.0MHz	-	4300	-	PF
Output Capacitance	C_{oss}		-	790	-	PF
Reverse Transfer Capacitance	C_{rss}		-	47	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,I_D=50A V_{GS}=10V,R_G=4.7Ω	-	13	-	nS
Turn-on Rise Time	t_r		-	58	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	39	-	nS
Turn-Off Fall Time	t_f		-	8	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=50A V_{GS}=10V	-	60	-	nC
Gate-Source Charge	Q_{gs}		-	21	-	nC
Gate-Drain Charge	Q_{gd}		-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=50A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	105	A
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=I_S di/dt=100A/μs (Note 3)	-	60	-	nS
Reverse Recovery Charge	Q_{rr}		-	140	-	nC

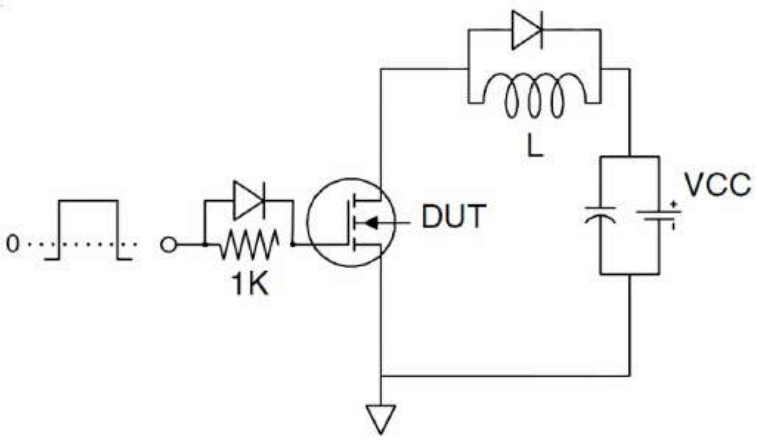
Notes:

① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t ≤ 10 sec.
③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
④ Guaranteed by design, not subject to production
⑤ EAS condition: Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω

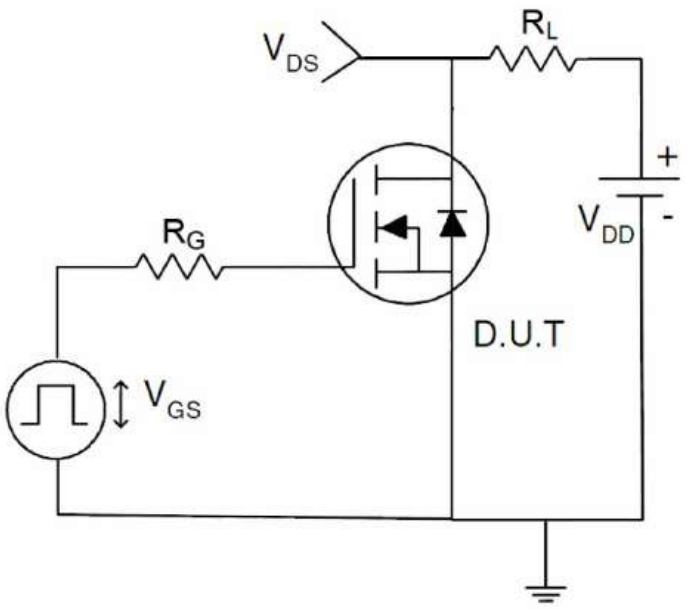
Test circuit



EAS test Circuit



Gate charge test Circuit



Switch Time Test Circuit

Typical Electrical and Thermal Characteristics (Curves)

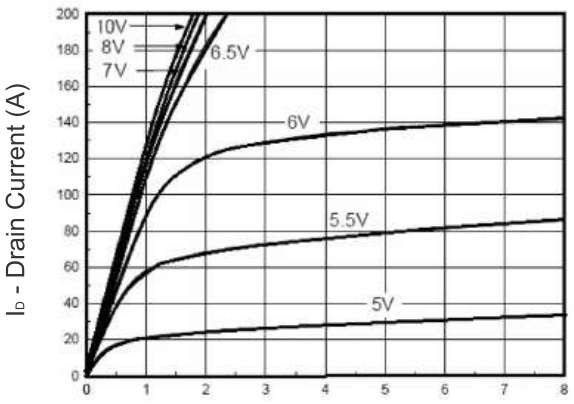


Figure 1 Output Characteristics

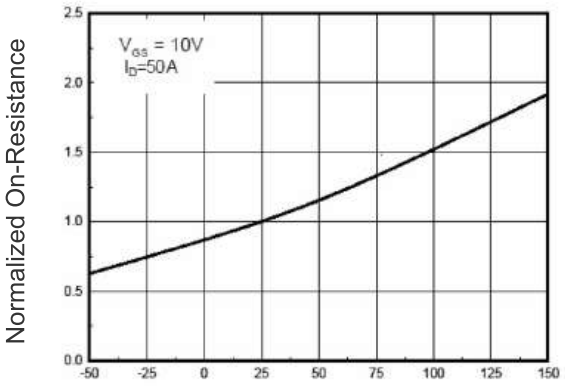


Figure 4 Rdson-Junction Temperature

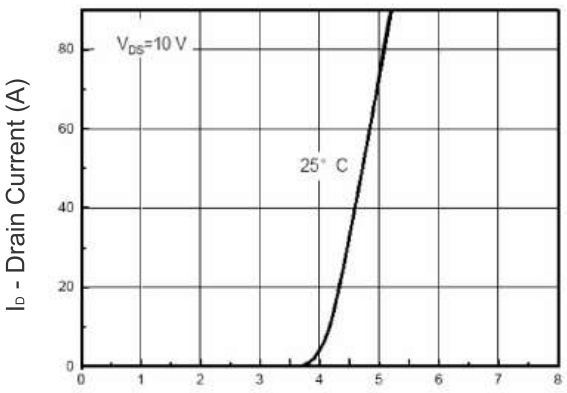


Figure 2 Transfer Characteristics

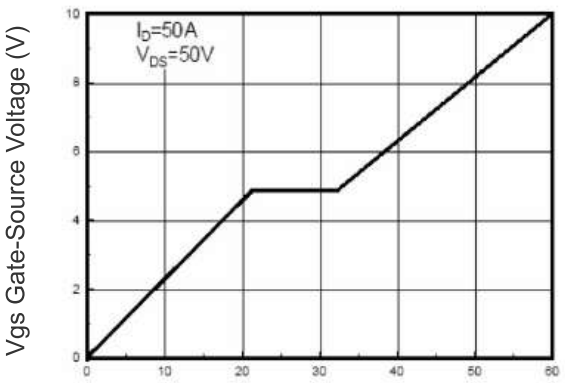


Figure 5 Gate Charge

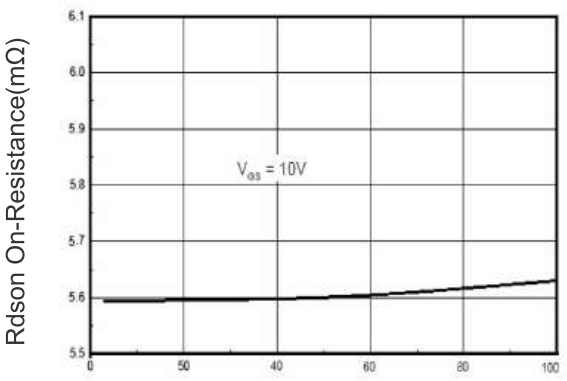


Figure 3 Rdson- Drain Current

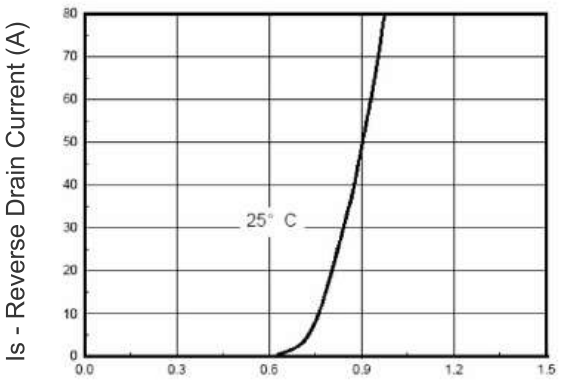


Figure 6 Source- Drain Diode Forward

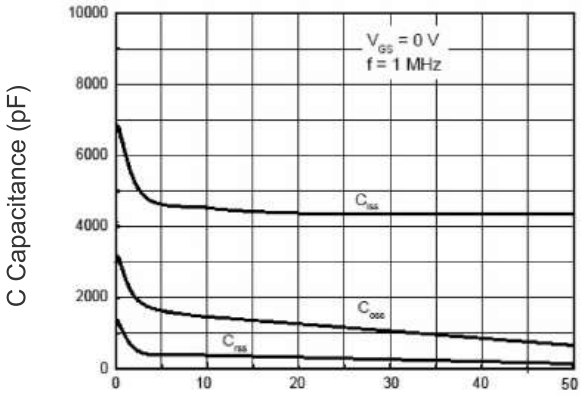


Figure 7 Capacitance vs Vds

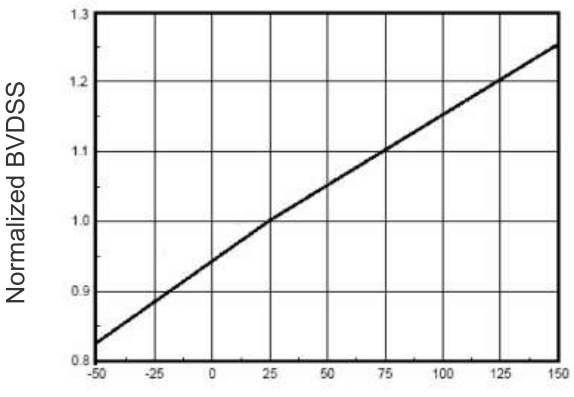


Figure 9 BV_{DSS} vs Junction Temperature

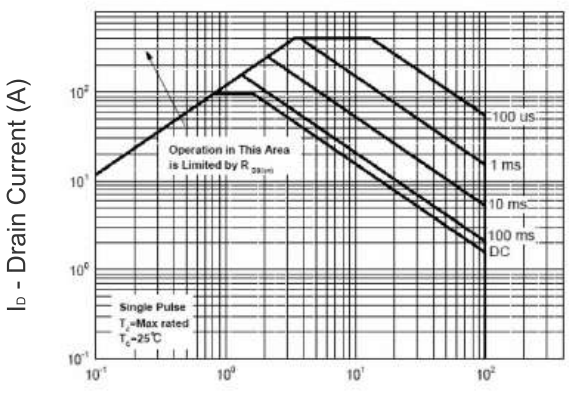


Figure 8 Safe Operation Area

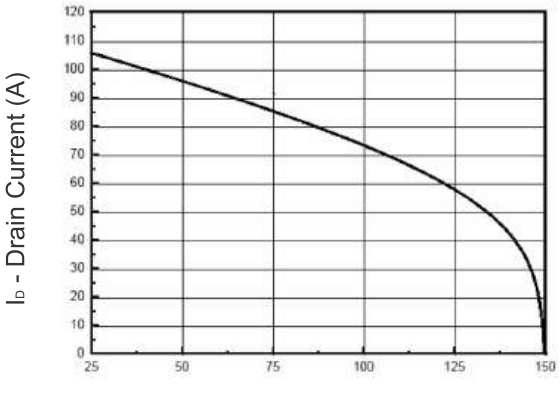


Figure 10 Current De-rating

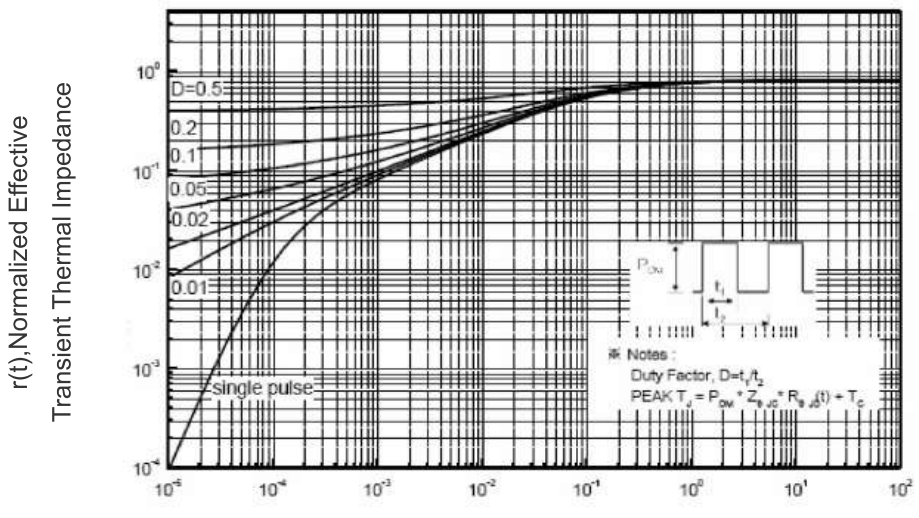
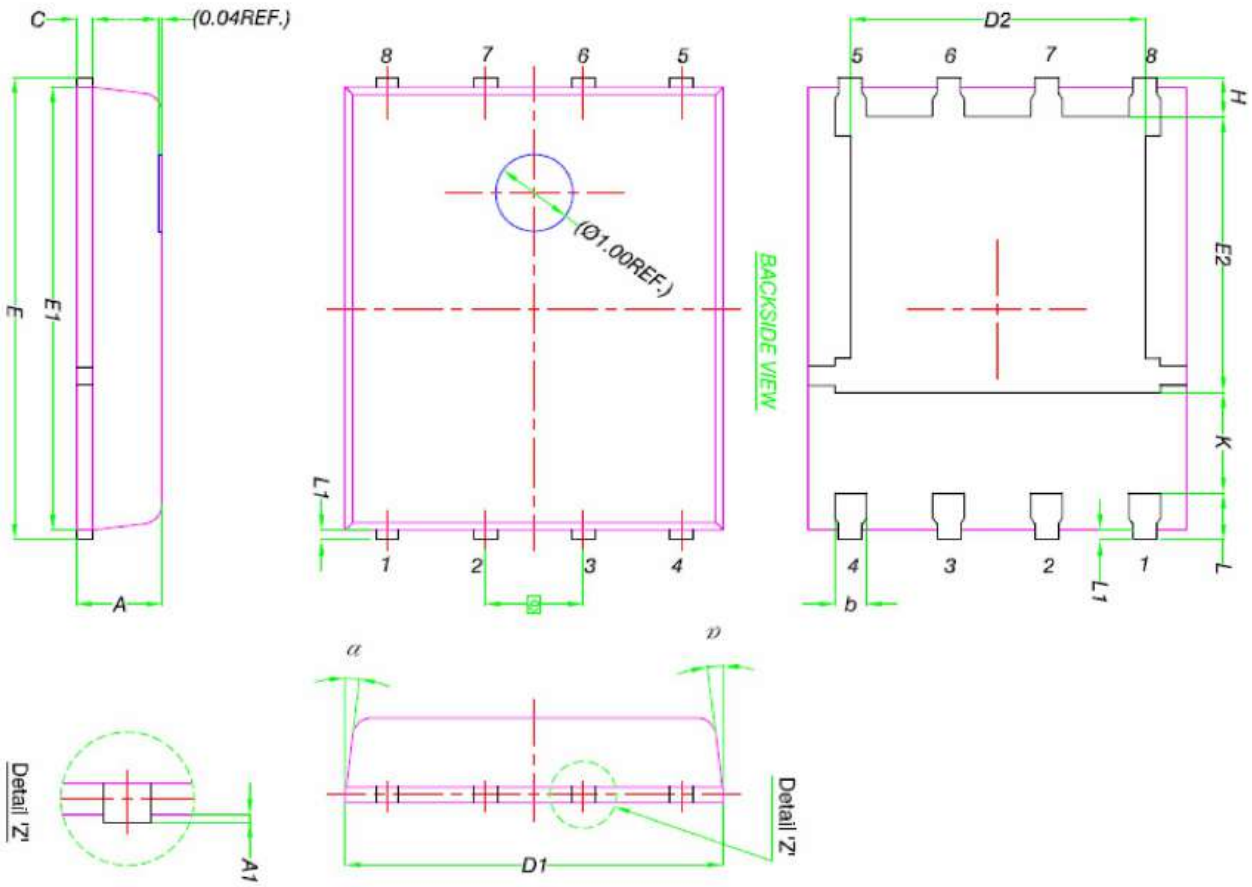
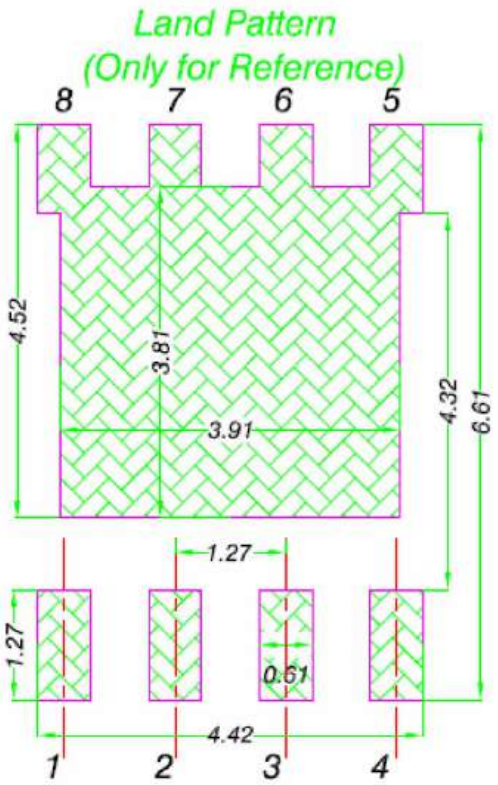


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



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